

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	512	427/503,496.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 22:30
L2	41	1 and contact near angle	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 22:30
L3	33	2 and @ad< "20021204"	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 22:30
L4	20	3 and electron near beam\$2	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 22:31
S1	0	"2001000415"	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/03 17:03
S2	1	"2001000415"	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/03 17:03
S3	1	contact near angle with silsesquioxane and electron near beam\$2	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 13:18
S4	0	contact near angle same oven same electron near beam\$2 same cur\$3 and electron near beam\$2	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 13:21
S5	0	contact near angle same oven same electron near beam\$2 same (cured or cure or curing)	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 13:22
S6	8	contact near angle same electron near beam\$2 same (cured or cure or curing)	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 13:22
S7	93	contact near angle same electron near beam\$2	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 13:24
S8	44	S7 and @ad< "20021204"	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 13:24
S9	24	S8 and (silicon or sod or silsesquioxane)	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 13:24
S10	27	S8 and (silicon or sod or silsesquioxane or dielectric)	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 13:26
S11	50	contact near angle same electron near beam\$2	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:31
S12	2	S11 and silsesquioxane	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:32
S13	90	contact with angle same electron near beam\$2	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:32
S14	2	S13 and silsesquioxane	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:32
S15	0	S13 and silicon with dielectric	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:36
S16	0	S13 and silicon and dielectric	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:36

S17	415	"111" and silicon and dielectric	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:36
S18	6070	"11" and silicon and dielectric	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:36
S19	0	S13 and silicon and dielectric	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:37
S20	1	"7030468".pn.	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:38
S21	52	(electron near beam\$2 or e near beam\$2) same contact near angle	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:41
S22	19341	(electron near beam\$2 or e near beam\$2) same (lower or decreas \$3) contact near angle	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:42
S23	6	(electron near beam\$2 or e near beam\$2) same (lower or decreas \$3) with contact near angle	FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:42
S24	29	(electron near beam\$2 or e near beam\$2) same (lower or decreas \$3) with contact near angle	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:42
S25	8	S24 and @ad< "20021204"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:45
S26	154	(electron near beam\$2 or e near beam\$2) same contact near angle	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:48
S27	81	S26 and @ad< "20021204"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:50
S28	0	S27 and dielectric and silicon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:54
S29	27	S27 and silicon	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 13:54
S30	2174	427/532,551,593,595.cds.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 14:29

S31	117	S30 and contact near angle	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 14:29
S32	53	S31 and @ad< "20021204"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 14:29
S33	27	S32 and (silicon or SOD or dielectric or silsesquioxane)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 14:30
S34	9812	427/331,372.2,384,387.cds.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 15:34
S35	5407	S34 and @ad< "20021204"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 15:34
S36	19480	"35" and contact near angle	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 15:36
S37	280	S35 and contact near angle	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 15:36
S38	179	S37 and (silicon or SOD or dielectric or silsesquioxane)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 15:36
S39	20	S38 and electron near beam\$2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	OFF	2008/12/04 15:36
S40	1	"5003178".pn.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/04 16:20

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